

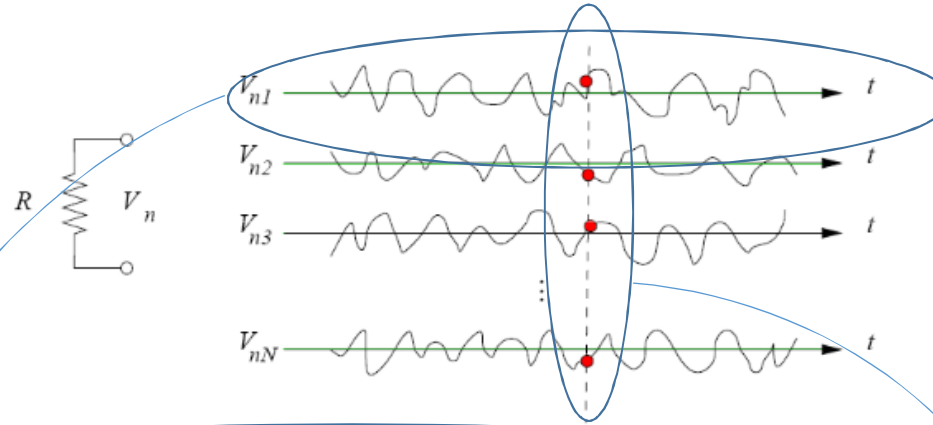
# Noise

Noise is represented as a random process

By definition random signals are unknown but they can be characterized by a few parameters or functions:

- Moments: average, variance
- Probability density function (PDF)
- Power Spectral density (PSD)

# Statistical Ensemble



Time Average :

$$\langle n(t) \rangle = \lim_{T \rightarrow \infty} \frac{1}{T} \int_{-T/2}^{T/2} n(t) dt$$

Mean square power :

$$\langle n^2(t) \rangle = \lim_{T \rightarrow \infty} \frac{1}{T} \int_{-T/2}^{T/2} n^2(t) dt$$

Ensemble Average :

$$\overline{n(t)} = \int_{-\infty}^{\infty} n(t) P_n(n) dn$$

Mean square power :

$$\overline{n^2(t)} = \int_{-\infty}^{\infty} n^2(t) P_n(n) dn$$

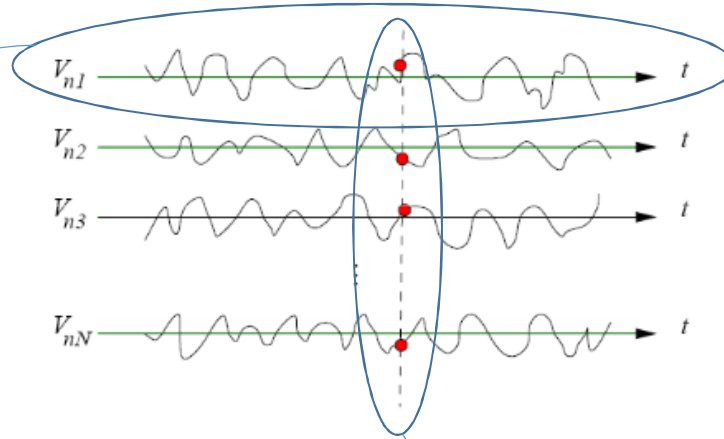
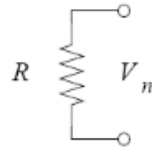
with  $P_n(n)$  the probability density function (PDF). If  $P_n$  is time-invariant the random process is stationary.

For our purposes :

$$\langle n(t) \rangle \approx \overline{n(t)} \approx 0$$

$$\langle n^2(t) \rangle \approx \overline{n^2(t)}$$

# Autocorrelation Function



Time average definition :

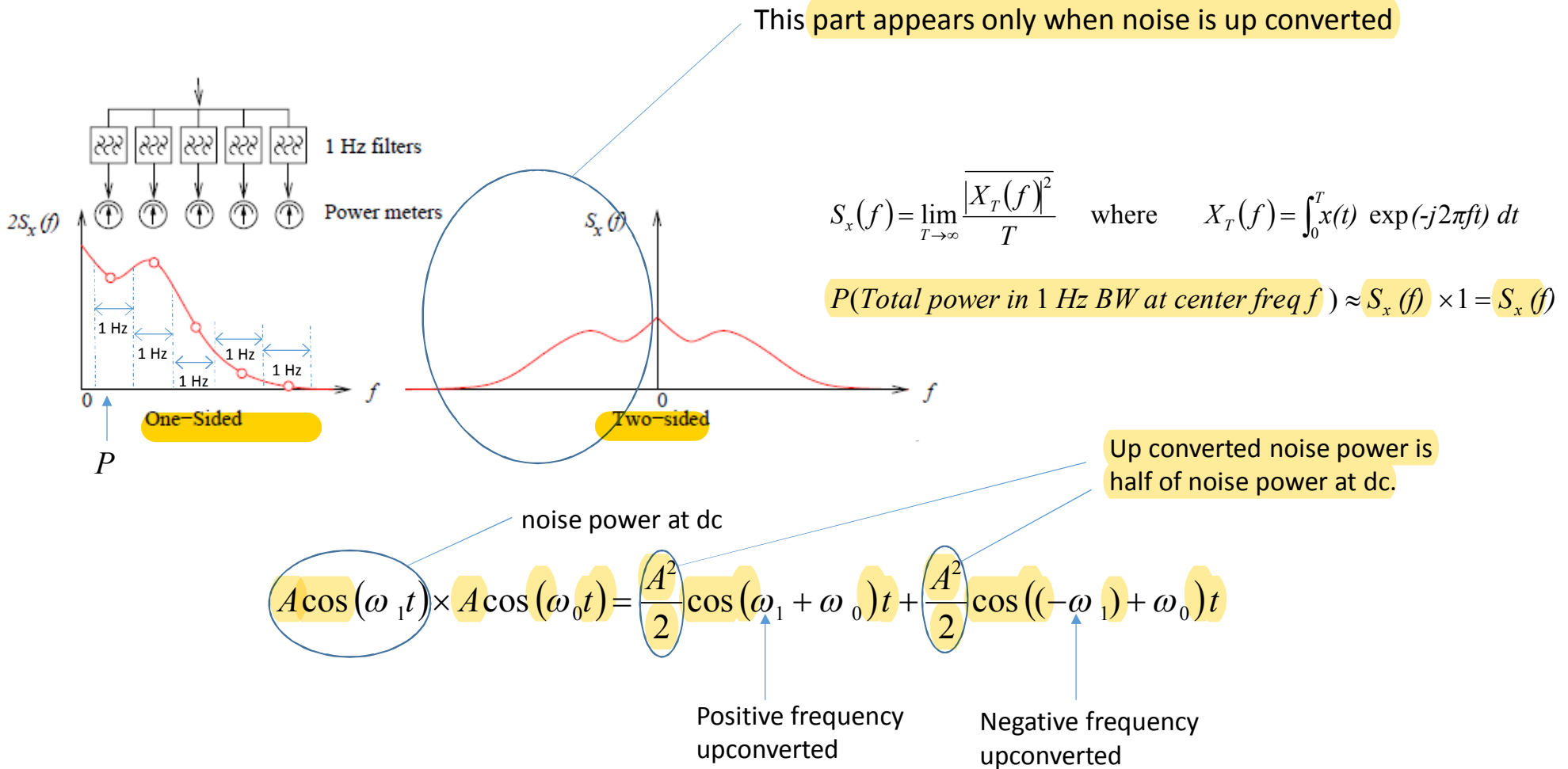
$$R(\tau) = \int_{-\infty}^{\infty} x^*(t)x(t+\tau)dt$$

Properties :  $R(-\tau) = R(\tau)$  and  $R(0) \geq R(\tau)$

Ensemble average definition for stationary random processes :

$$R(\tau) = \overline{x^*(t)x(t+\tau)} = \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} x_1 x_2 P_x(x_1, x_2, \tau) dx_1 dx_2$$

# Power Spectral density



# Wiener Khintchine Theorem

Relates autocorrelation and power spectral density.

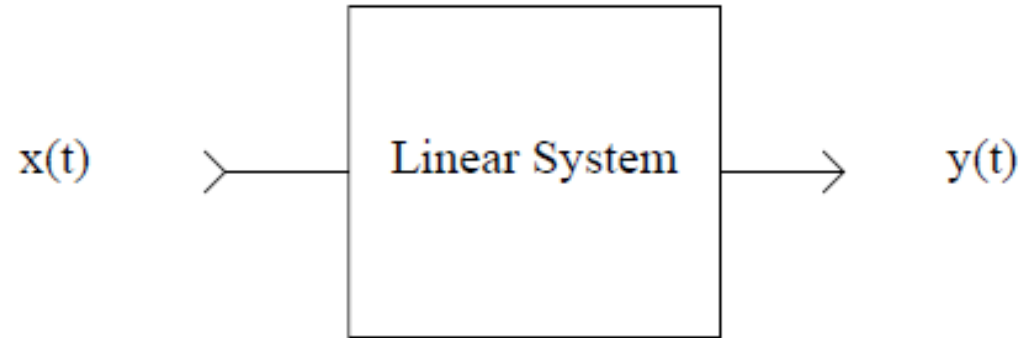
If for a stationary process we have  $\int_{-\infty}^{\infty} |\tau R(\tau)| d\tau < \infty$  then,

$$S_x(f) = \int_{-\infty}^{\infty} R(\tau) \exp(-j2\pi f \tau) d\tau \quad \text{or} \quad R(\tau) = \int_{-\infty}^{\infty} S_x(f) \exp(j2\pi f \tau) df$$

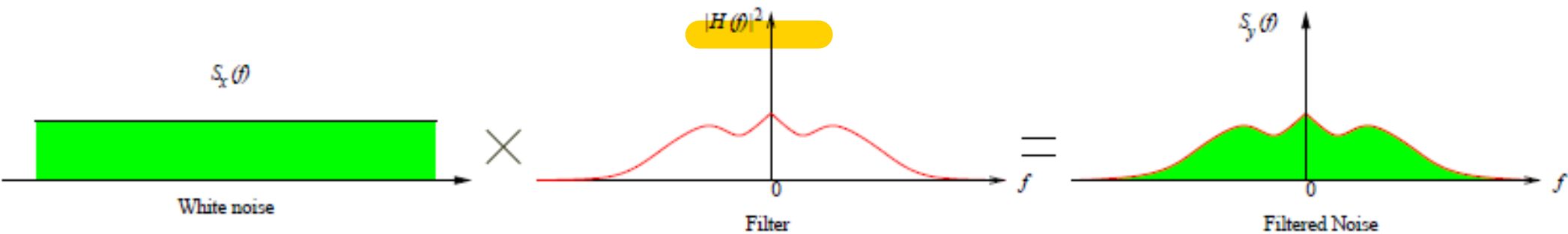
In particular the power in a  $1\Omega$  load is :

$$P_L = \overline{x^2(t)} = R(0) = \int_{-\infty}^{\infty} S_x(f) df$$

# Noise in Linear Systems



$$S_y(f) = |H(f)|^2 S_x(f)$$



# Sources of noise

- External sources of noise (temperature) at the antenna (measured in Kelvin)
  - natural
  - man-made
- Receiver or transmitter noise (temperature or noise figure)

## Types of noise:

- Thermal or Johnson or Nyquist noise (PDF: Gaussian, PSD: white noise)
- Shot noise (PDF: Poisson, PSD: white)
- Flicker noise (PDF: Gaussian, PSD:  $1/f$ )
- Quantum noise (PDF: Poisson, PSD:  $f$ )

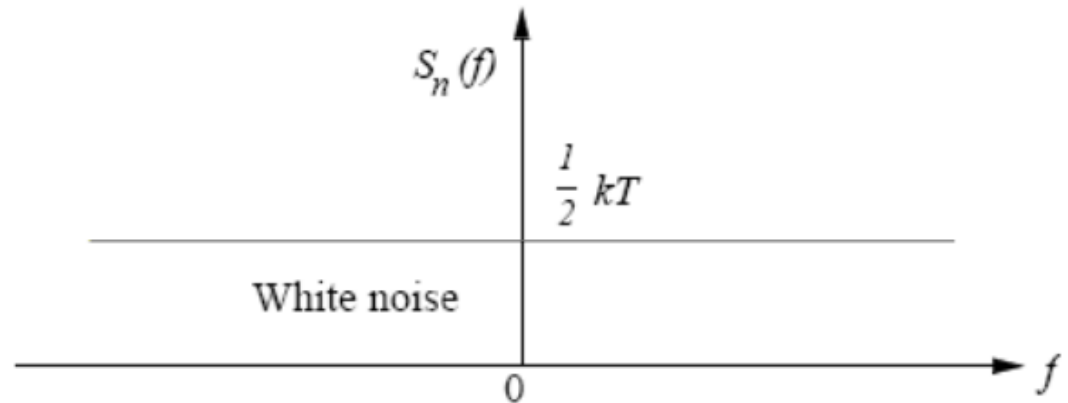
# Ideal Thermal Noise

The power spectral density is constant and extends upto infinite frequencies  
(white noise)

$$S_n(f) = \frac{kT}{2}$$

Autocorrelation :

$$R(\tau) = \int_{-\infty}^{\infty} \frac{kT}{2} \exp(j2\pi ft) df = \frac{kT}{2} \delta(\tau)$$

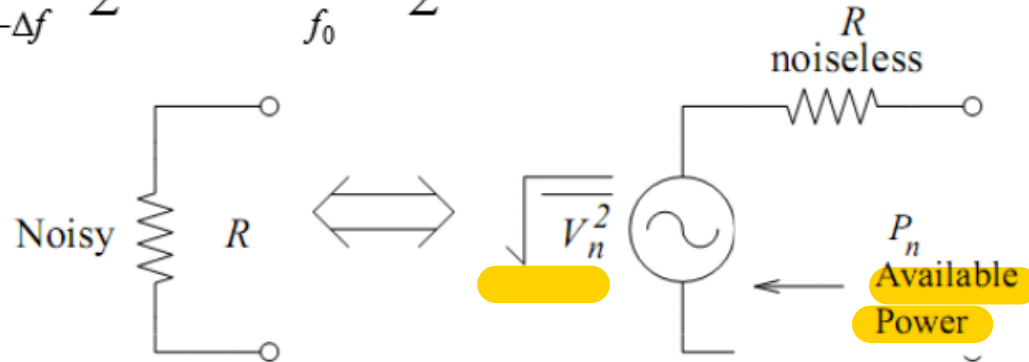




# Thermal Noise RMS voltage

Available (maximum) noise power in bandwidth  $\Delta f$  :

$$P_n = \int_{-f_0 - \Delta f}^{-f_0} \frac{kT}{2} df + \int_{f_0}^{f_0 + \Delta f} \frac{kT}{2} df$$

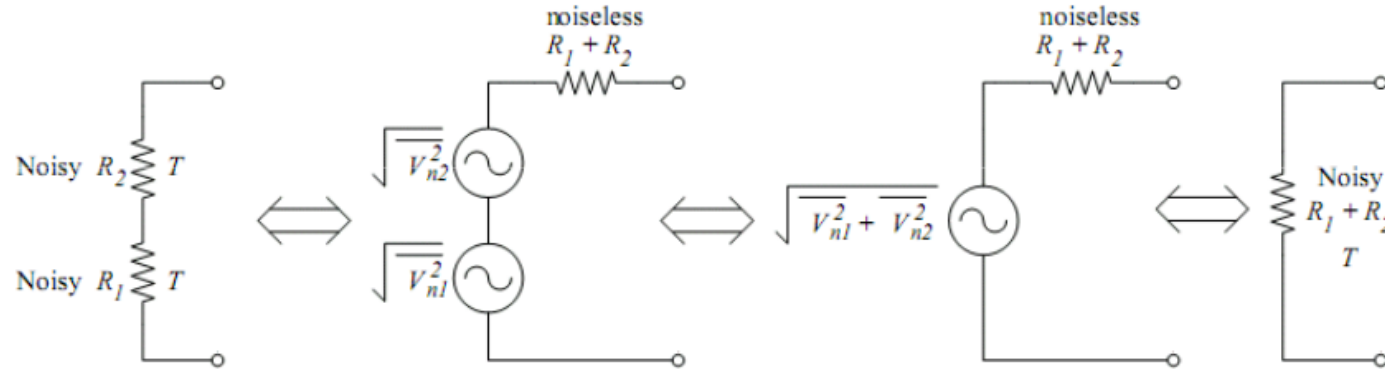


The available (maximum) power is obtained for a conjugate matched load  $R$

The maximum power delivered is then given by

$$P_n = kT\Delta f = \left( \frac{\sqrt{V_n^2}}{2R} \right)^2 R = \frac{V_n^2}{4R} \Rightarrow \sqrt{V_n^2} = \sqrt{4kTR\Delta f}$$

# Noisy Resistors in series



**Total available noise power** (need a load  $R_1 + R_2$ ):

$$P_{n,\text{total}} = (R_1 + R_2) \left( \frac{1}{2} \frac{\sqrt{\overline{V_{n1}^2}}}{(R_1 + R_2)} \right)^2 + (R_1 + R_2) \left( \frac{1}{2} \frac{\sqrt{\overline{V_{n2}^2}}}{(R_1 + R_2)} \right)^2 = kT\Delta f$$

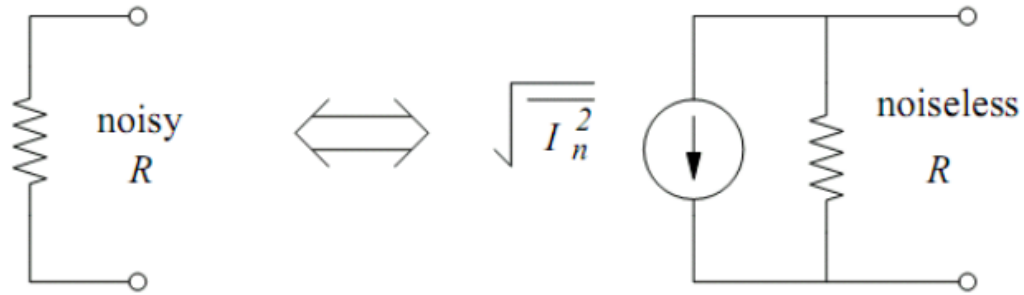
using  $\overline{V_{n1}^2} = 4kTR_1\Delta f$  and  $\overline{V_{n2}^2} = 4kTR_2\Delta f$

The total rms voltage is obtained by adding the square of the rms voltages :

$$\overline{V_{n,\text{total}}^2} = \overline{|V_{n1} + V_{n2}|^2} = \overline{V_{n1}^2} + \overline{V_{n2}^2} = 4kT(R_1 + R_2)\Delta f$$

This is due to the fact that  $V_{n1}$  and  $V_{n2}$  are uncorrelated

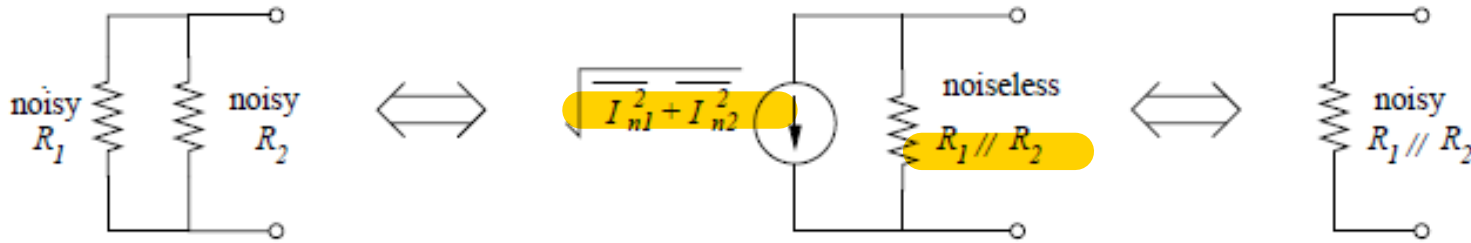
# Current Representation



Norton current source representation :

$$\sqrt{I_n^2} = \sqrt{4kT \frac{1}{R} \Delta f}$$

# Resistors In Shunt



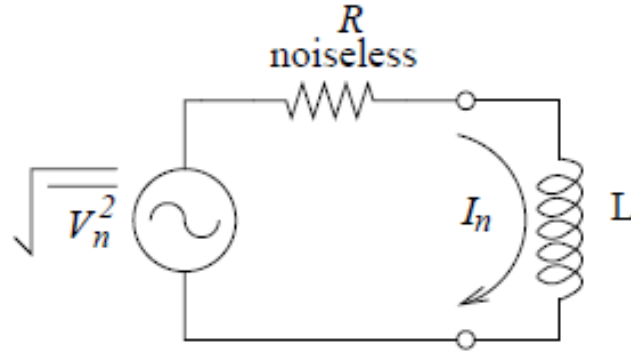
Total available noise power is still  $P_n = kT\Delta k$  and is obtained for a load termination  $R_1 \parallel R_2$ .

The total rms current is obtained by adding the square of the rms current :

$$\overline{I_{n,\text{total}}^2} = \overline{|I_{n1} + I_{n2}|^2} = \overline{I_{n1}^2} + \overline{I_{n2}^2} = 4kT \frac{1}{R_1 \parallel R_2} \Delta f$$

This is due to the fact that  $I_{n1}$  and  $I_{n2}$  are uncorrelated

# Noise Shaping Example: RL Circuit



The PSD of the voltage  $V_n$  generated by the resistor  $R$  is:  $S_V = 4kTR$

The square of the voltage - current transfer function is:  $|H(f)|^2 = \frac{1}{R^2 + \omega^2 L^2}$

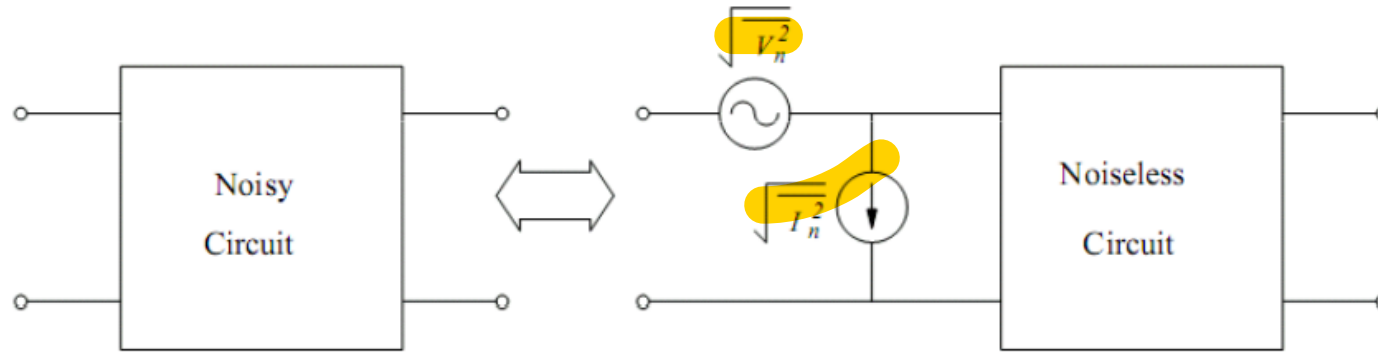
The PSD of the current is then:  $S_I = S_V |H(f)|^2 = \frac{4kTR}{R^2 + \omega^2 L^2}$  and the rms current  $\overline{I_n^2}$  is

(considering +ve frequencies only):

$$\overline{I_n^2} = \int_0^\infty S_I df = \int_0^\infty S_V |H(f)|^2 df = S_V \int_0^\infty \frac{1}{R^2 + \omega^2 L^2} df = \frac{kT}{L}$$

An inductor is a noise less component but it can store noise energy:  $\frac{1}{2} L \overline{I_n^2} = \frac{1}{2} kT$

# Input Referred Noise

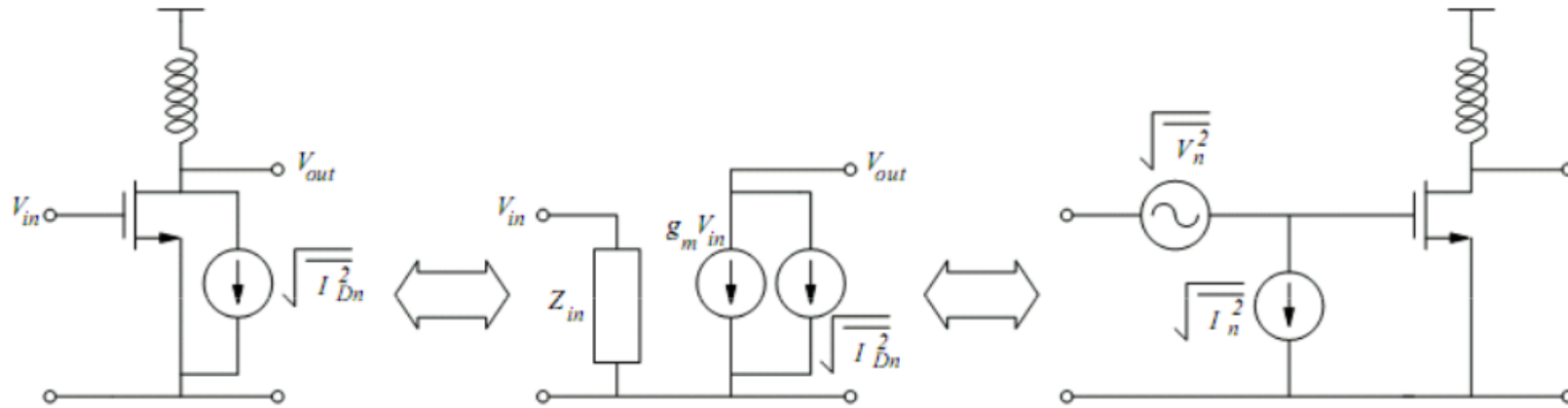


All noise sources in a 2 port network can be moved to the input. See App L of Gonzalez for conversion formula.

# Example of Input Referred Noise

For a MOSFET in saturation the dominant noise is thermal noise in the channel:

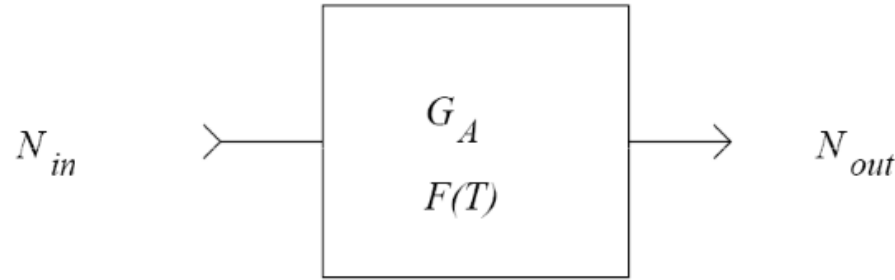
$$\overline{I_{Dn}^2} = 4kT \frac{2}{3} g_m$$



Shorting the input :  $g_m^2 \overline{V_n^2} = \overline{I_{nD}^2}$  gives  $\overline{V_n^2} = \frac{8kT}{3g_m}$

Leaving the input open :  $g_m^2 \overline{I_n^2} |Z_{in}|^2 = \overline{I_{nD}^2}$  gives  $\overline{I_n^2} = \frac{8kT}{3g_m |Z_{in}|^2}$

# Noise Figure and SNR ratio



Property : F is equal to the Input to Output Signal to noise ratio :

$$F = \frac{SNR_{in}}{SNR_{out}}$$

Power Available from amplifier at o/p

$$SNR_{out} = \frac{S_{out}}{N_{out}} \text{ with } S_{out} \text{ the input signal power}$$

$N_{in}$  and  $N_{out}$  are the i/p and o/p noise powers

Power Available from Source

$$SNR_{in} = \frac{S_{in}}{N_{in}} \text{ with } S_{in} \text{ the output signal power}$$

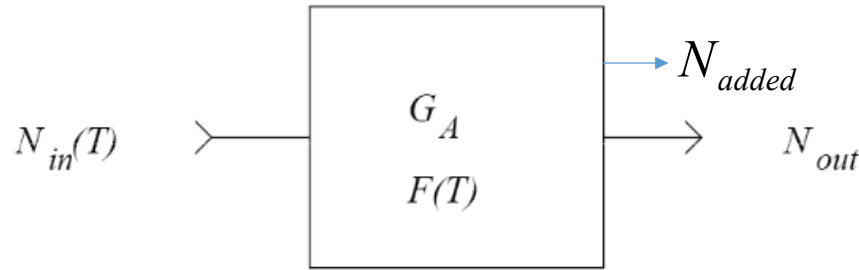
Available Power gain

$$F = \frac{SNR_{in}}{SNR_{out}} = \frac{S_{in}}{N_{in}} \frac{N_{out}}{S_{out}} = \frac{N_{out}}{N_{in} G_A}$$

using :  $G_A = \frac{S_{out}}{S_{in}}$



# Noise Figure



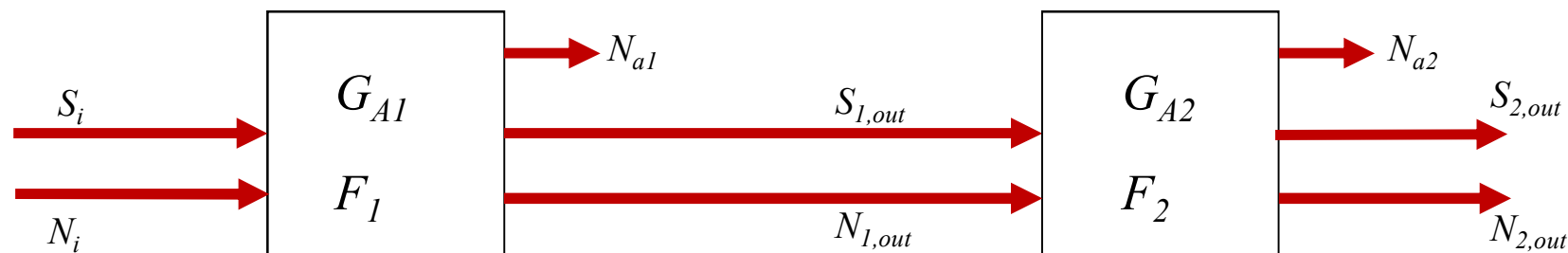
Noise Figure :  $F = NF = \frac{N_{out}}{N_{in} G_A}$  with :

Properties :

- $F \geq 1$
- $F = 1$  for zero added noise power  $N_{added} = 0$  (ideal device)
- $F(T_0)$  is usually given for an input noise source at room temperature

$$N_{out} = G_A N_{in} + N_{added}$$

# Cascaded Network



$$N_{1,out} = N_{a1} + G_{A1} N_i$$

$$N_{2,out} = N_{a2} + G_{A2} (N_{a1} + G_{A1} N_i)$$

$$S_{1,out} = G_{A1} S_i$$

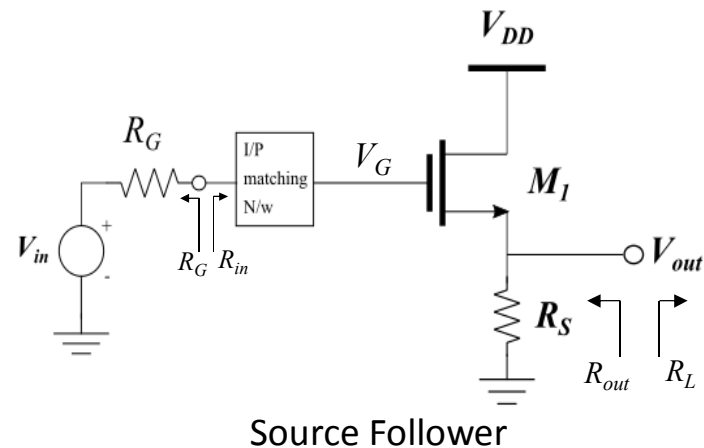
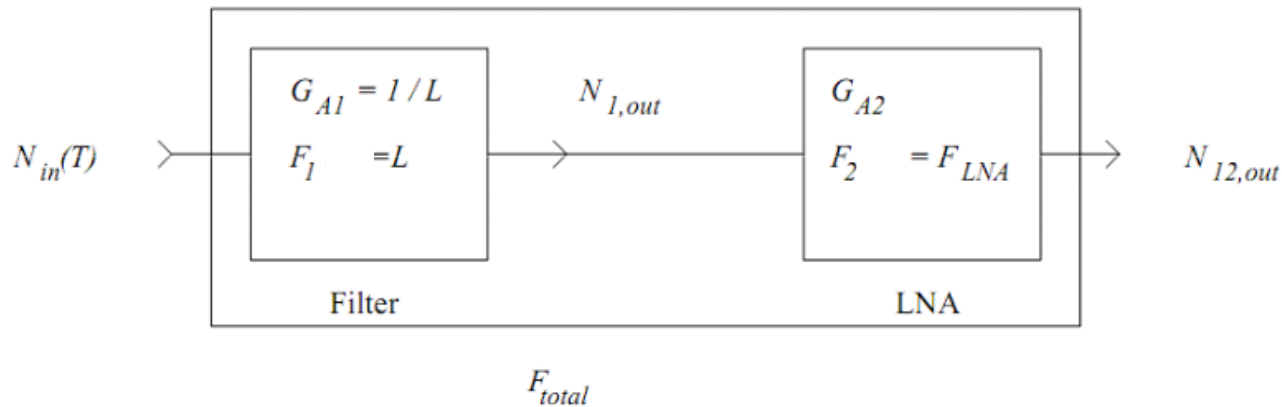
$$S_{2,out} = G_{A1} G_{A2} S_i$$

$$F_1 = \frac{SNR_{in}}{SNR_{out,1}} = \frac{S_i / N_i}{S_{1,out} / N_{1,out}} = \frac{N_{a1} + G_{A1} N_i}{G_{A1} N_i} = 1 + \frac{N_{a1}}{G_{A1} N_i}$$

$$\text{Similarly, } F_2 = 1 + \frac{N_{a2}}{G_{A2} N_i}$$

$$F_{total} = \frac{SNR_{in}}{SNR_{out,2}} = \frac{S_i / N_i}{S_{2,out} / N_{2,out}} = \frac{N_{a2} + N_{a1} G_{A2} + G_{A2} G_{A1} N_i}{G_{A2} G_{A1} N_i} = 1 + \frac{N_{a1}}{N_i G_{A1}} + \frac{N_{a2}}{N_i G_{A1} G_{A2}} = F_1 + \frac{F_2 - 1}{G_{A1}}$$

# Filter in cascade with LNA



Total Noise Figure :

$$F_{\text{total}} = F_{\text{filter}} + \frac{F_{\text{LNA}} - 1}{G_{A1}} = L + \frac{F_{\text{LNA}} - 1}{1/L} = L \times F_{\text{LNA}}$$

using  $G_{A1} = G_{\text{filter}} = 1/L$

Just need to add the noise figures in dB :

$$F_{\text{total}} |_{\text{dB}} = L |_{\text{dB}} + F_{\text{LNA}} |_{\text{dB}}$$

Say,  $R_G = R_{in} = R_{out} = R_L = 50\Omega$

$$V_G = \alpha V_{in} \quad (\alpha < 1)$$

$$V_{out} = \frac{g_m(R_S \parallel R_L)}{1 + g_m(R_S \parallel R_L)} V_G = \frac{g_m(R_S \parallel R_L)}{1 + g_m(R_S \parallel R_L)} \alpha V_{in}, \quad [\text{Neglecting } r_o]$$

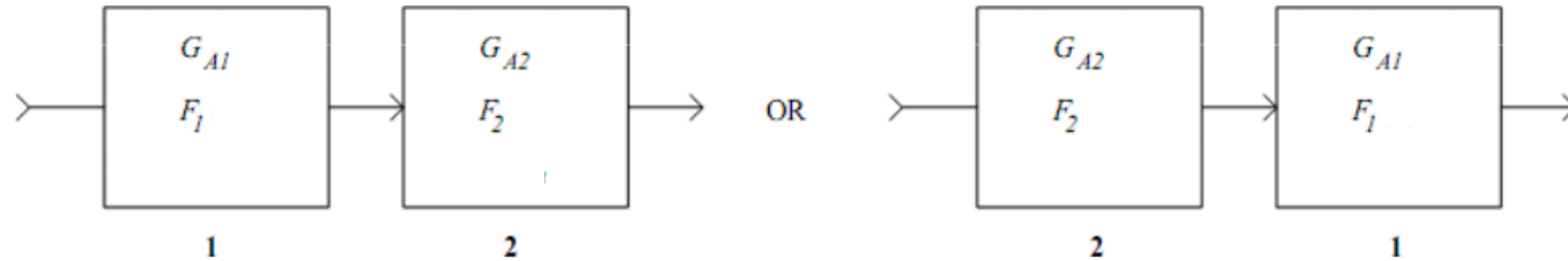
$$\Rightarrow \frac{V_{out}^2}{V_{in}^2} = \frac{g_m^2(R_S \parallel R_L)^2}{[1 + g_m(R_S \parallel R_L)]^2} \alpha^2$$

$$\Rightarrow \frac{P_{AVN}}{P_{AVS}} = G_A = \frac{g_m^2(R_S \parallel R_L)^2}{[1 + g_m(R_S \parallel R_L)]^2} \alpha^2 < 1$$

Attenuation

$$P_{AVN} = \frac{V_{out}^2 R_{out}}{(2R_{out})^2}, \quad P_{AVS} = \frac{V_{in}^2 R_G}{(2R_G)^2}$$

# Cascade Ordering and Noise Measure



we need to have :

$$F_{12} < F_{21}$$

$$F_1 + \frac{F_2 - 1}{G_{A1}} < F_2 + \frac{F_1 - 1}{G_{A2}}$$

$$M_1 = \frac{F_1 - 1}{1 - \frac{1}{G_{A1}}} < \frac{F_2 - 1}{1 - \frac{1}{G_{A2}}} = M_2$$

$M_1$  and  $M_2$  are called the noise measure.

# Optimum source admittance $Y_s$

The noise figure is a function of the source admittance  $Y_s$  and  $Y_{opt}$  can be rewritten as :

$$F(Y_s) = F_{\min} + \frac{R_n}{G_s} |Y_s - Y_{opt}|^2$$

where we have :

$$Y_{opt} = G_{opt} + jB_{opt}$$

- $Y_{opt}$  is the optimal source admittance at which the noise figure is minimum :

$$F(Y_{opt}) = F_{\min}$$

- The locus of constant noise factor in the admittance plane  $Y_s$ , are circles centered around  $Y_{opt}$ .

# Noise Figure in terms of reflection coefficients

The noise figure can be rewritten as a function of **normalized admittances**

$y_s$  and  $y_{opt}$  as :

$$F(Y_s) = F_{\min} + \frac{r_n}{g_s} |y_s - y_{opt}|^2$$

where we have :

$$y_{opt} = \frac{Y_{opt}}{Y_0} = g_{opt} + jb_{opt}, \quad r_n = \frac{R_n}{Z_0}$$

$$y_s = \frac{Y_s}{Y_0} = g_s + jb_s, \quad \frac{Z_{opt} - Z_0}{Z_{opt} + Z_0} = \frac{Y_0 - Y_{opt}}{Y_0 + Y_{opt}} = \frac{y_{opt} - 1}{y_{opt} + 1} \Rightarrow y_{opt} = \frac{1 + \Gamma_{opt}}{1 - \Gamma_{opt}}, \quad y_s = \frac{1 + \Gamma_s}{1 - \Gamma_s}$$

The noise figure can then be rewritten as a function of reflection coefficients

$\Gamma_s$  and  $\Gamma_{opt}$  as :

$$F(Y_s) = F_{\min} + \frac{4r_n |\Gamma_s - \Gamma_{opt}|^2}{(1 - |\Gamma_s|^2) |1 + \Gamma_{opt}|^2}$$

# Constant Noise Figure Circles

The noise figure  $F(\Gamma_s) = F_{\min} + \frac{4r_n |\Gamma_s - \Gamma_{\text{opt}}|}{(1 - |\Gamma_s|^2) |1 + \Gamma_{\text{opt}}|^2}$

can be rewritten :

$$N_i = \frac{F_i - F_{\min}}{4r_n} \times |1 + \Gamma_{\text{opt}}|^2 = \frac{|\Gamma_s - \Gamma_{\text{opt}}|^2}{1 - |\Gamma_s|^2}$$

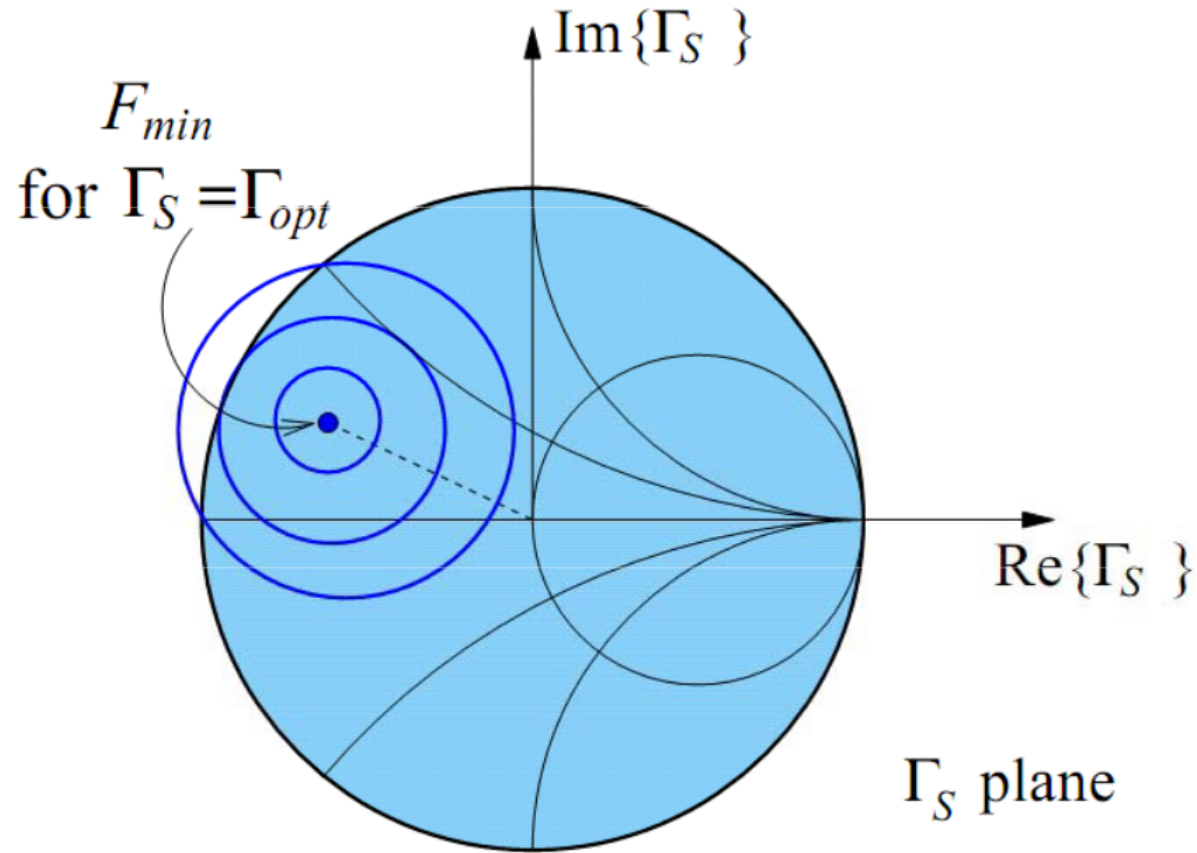
After some mathematical derivations we obtain the equation of a circle :

$$|\Gamma_s - C_i| = R_i$$

with :

$$C_i = \frac{\Gamma_{\text{opt}}}{1 + N_i} \quad \text{and} \quad R_i = \frac{\sqrt{N_i^2 + N_i(1 - |\Gamma_{\text{opt}}|^2)}}{1 + N_i}$$

# Constant Noise Figure Circles





# Noise, Gain and DC power Trade-Off in RFICs

Need for an input matching trade - off (using for example M) :

- The minimum noise figure occurs for  $Y_s = Y_{opt}$
- The maximum available power gain  $G_A(Y_s)$  occurs for  $Y_s = Y_{s,M}$  (assuming device is stable)

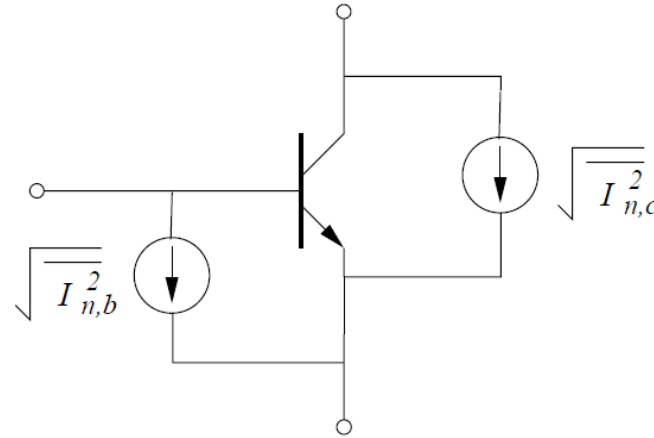
RFIC specific design issues :

- Both the bias point and the device size can be optimized in RFICs to optimize,
  - the maximum power gain
  - $F_{min}$
  - IP3 (SFDR)
- In cellular phone, talk time requires that we set a constraint on the power dissipation of the LNA : requiring a power constraint on the optimization.

# Other Types of Noise Source: Shot Noise

Shot noise (Poisson process:  $\overline{m(t)^2} - (\overline{m(t)})^2 = \overline{m(t)}$ ) noise associated with the corpuscular nature of the electron (charge  $q$ ) and its emission over a barrier (PN and Schottky diode, BJT). Shot noise is proportional to the DC current  $I$ :

$$\overline{I_n^2} = 2qI\Delta f$$



- $\sqrt{\overline{I_n^2}}$  is about 18 pA/  $\sqrt{\text{Hz}}$  for 1 mA of  $I$
- Shot noise is to be added to the thermal noise arising from the base  $r_b$  and emitter  $r_e$  resistance s.

# Other Types of Noise Sources: 1/f noise in MOSFETs

Trapping and release of charges in the oxide with different time constants leads to Flicker noise:

$$\overline{I_n^2} = \frac{K}{W_g L_g C_{ox}} \frac{1}{f} \Delta f$$

- The corner frequency is the frequency at which the 1/f noise is equal to the thermal noise.
- A lower corner frequency is desirable.
- MOSFETs have corner frequencies around 10 KHz to 1 MHz (BJT : 10 - 100 Hz).
- 1/f (pink noise) is to be added to the thermal noise in the FET channel (drain) and gate channel noise.
- See notes from Oslo university about noise calculation in BJT's and MOSFETs's.

# Receiver Sensitivity

The sensitivity is the minimum input signal level which can be detected with an acceptable output SNR ( $SNR_{min}$ ) for an input noise at room temperature  $T_0$ .

$$SNR_{out} \geq SNR_{min}$$

using  $F = \frac{SNR_{in}}{SNR_{out}}$  this gives

$$SNR_{out} = \frac{S_{out}}{N_{out}} = \frac{1}{F} SNR_{in} = \frac{1}{F} \frac{S_{in}}{N_{in}} \geq SNR_{min}$$

*Min SNR needed for baseband processing*

So the minimum distinguishable signal :

$$P_{i, mds} = S_{in, min} = N_{in} \cdot F \cdot SNR_{min} = kT_0 \Delta f \cdot F \cdot SNR_{min}$$

In dBm this gives a sensitivity of :

$$S_{in, min} |_{dB} = 10 \log(kT_0) + 10 \log(\Delta f |_{Hz}) + F |_{dB} + SNR_{min} |_{dB}$$

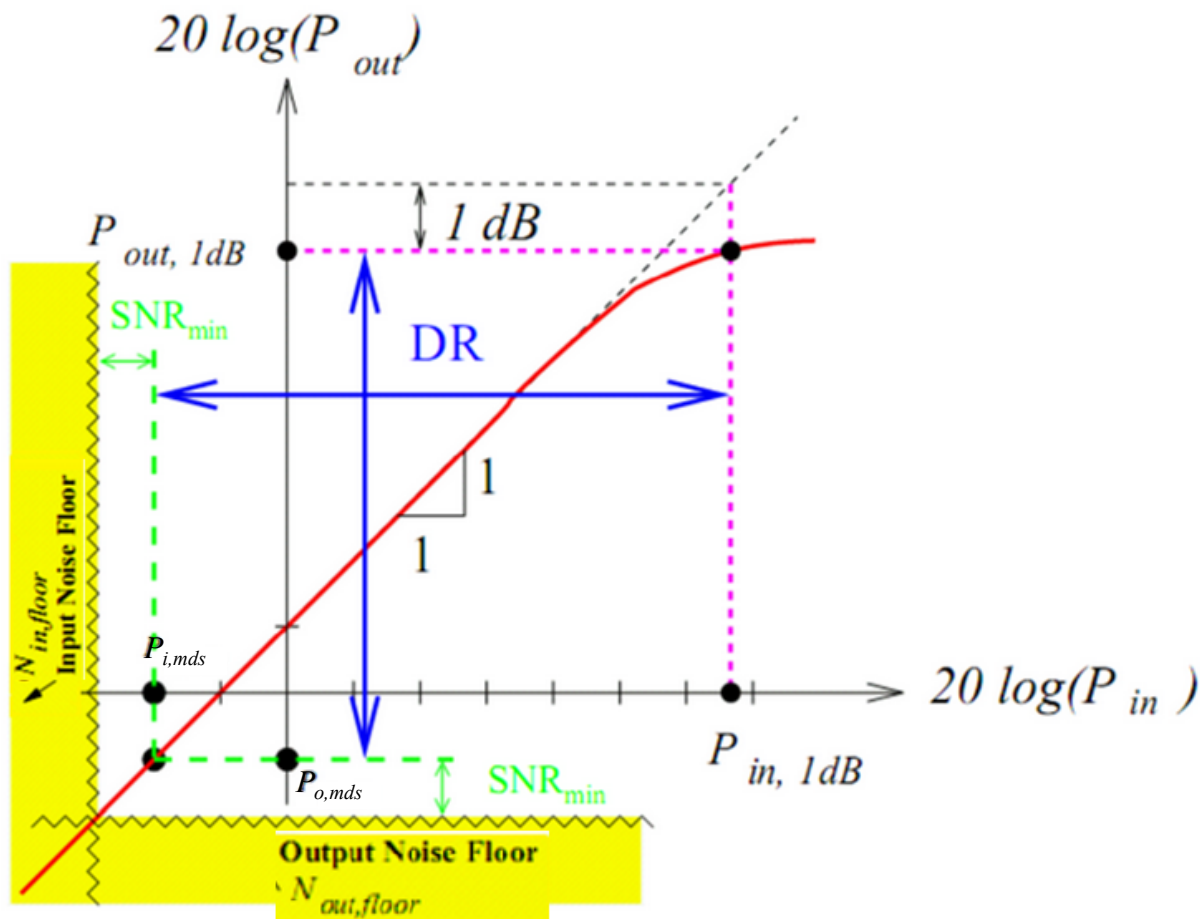
$$= N_{in, floor} |_{dB} + SNR_{min} |_{dB} = P_{i, mds} |_{dB}$$

where  $N_{in, floor}$  is the input referred noise floor ( $SNR_{min} = 0$ )

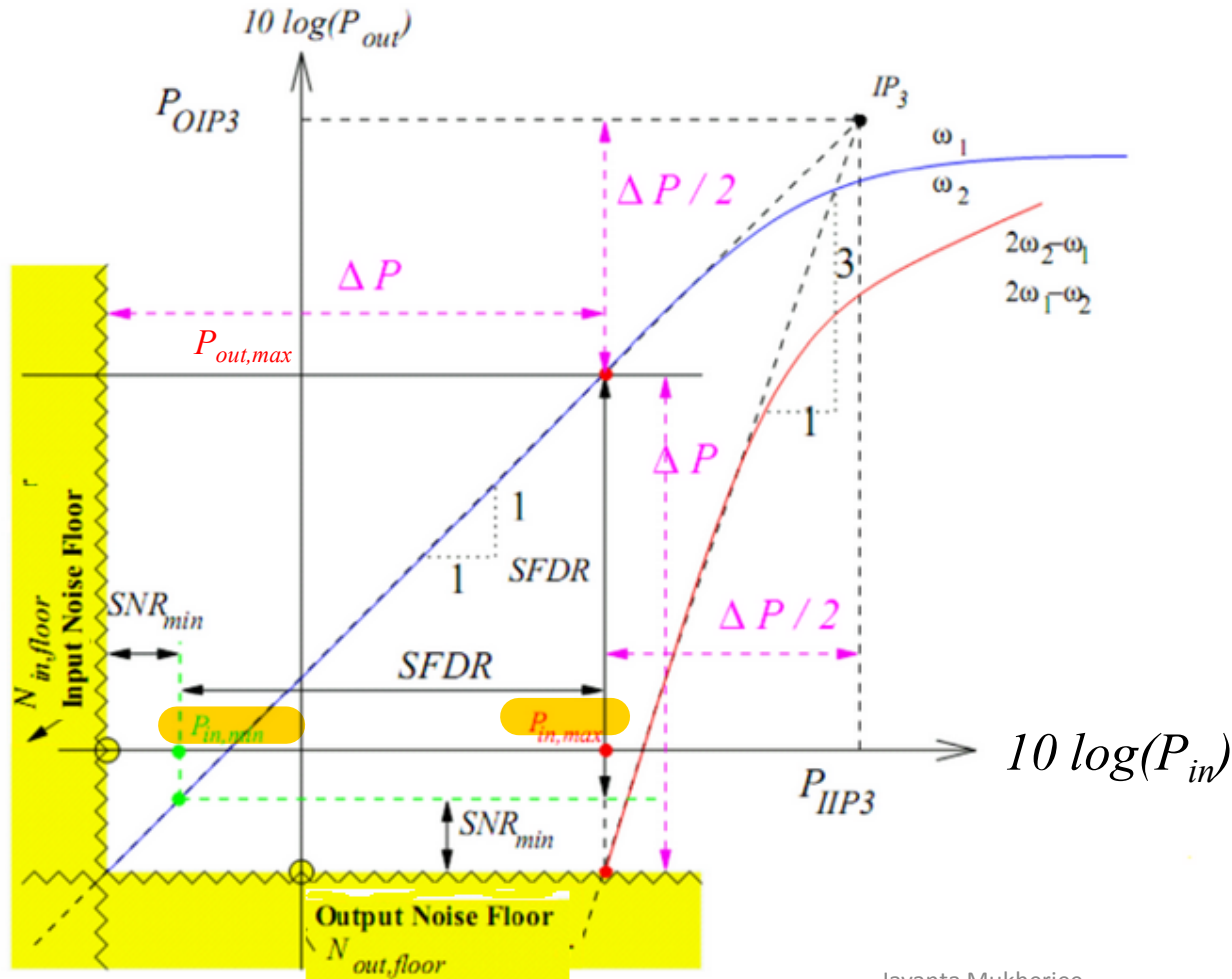
$$N_{in, floor} |_{dBm} = -174 dBm / Hz + 10 \log(\Delta f |_{Hz}) + F |_{dB}$$

# Dynamic Range

$$DR = P_{out,1dB} - P_{o,mds} = P_{in,1dB} - P_{i,mds}$$



# Spurious Free Dynamic Range (SFDR)



# Spurious Free Dynamic Range (Contd..)

$$SFDR = P_{in,max}|_{dB} - P_{in,min}|_{dB}$$

Since we have (all in dB)

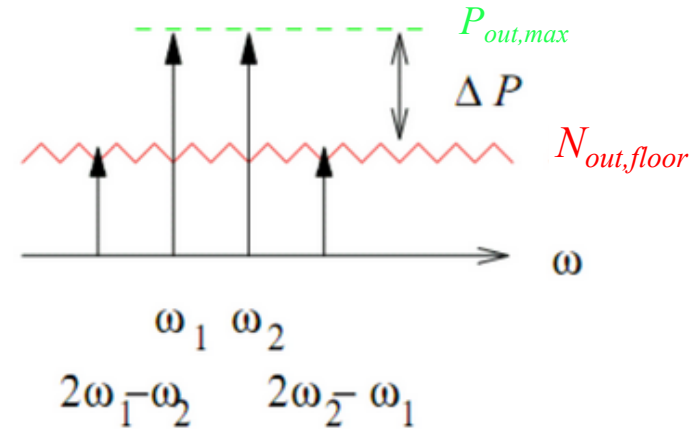
$$P_{IIP3} = P_{in,max} + \frac{\Delta P}{2} = P_{in,max} + \frac{P_{in,max} - N_{in,floor}}{2}$$

we can therefore solve for  $P_{in,max}$  :

$$P_{in,max} = \frac{2P_{IIP3} + N_{in,floor}}{3}$$

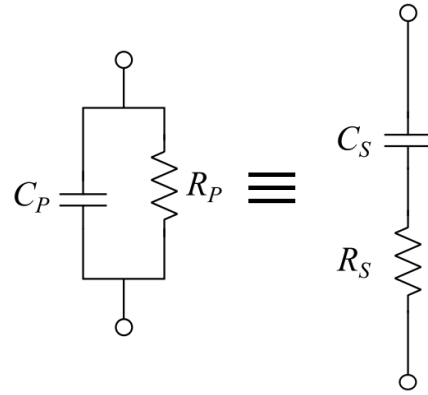
Resulting in the SFDR

$$SFDR = P_{in,max}|_{dB} - P_{in,min}|_{dB} = \frac{2(P_{IIP3}|_{dB} - N_{in,floor}|_{dB})}{3} - SNR_{min}|_{dB}$$



# Matching Networks

Consider the following circuit with  $R_S \ll R_P$  :



Both circuits have the same impedance at  $\omega$  when :

$$C_S \approx C_P \quad \text{and} \quad R_S \approx \frac{1}{R_P (C_P \omega)^2} \Rightarrow R_P \approx \frac{1}{R_S (C_S \omega)^2}$$

· Can be used to decrease  $R_P$  to a lower value or increase  $R_S$  to a higher value.



# High Q Circuits Used for Increasing $R_p$

